

General Description

The AON6405L combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

Features

$$V_{DS} (V) = -30V$$

$$I_D = -30A \quad (V_{GS} = -10V)$$

$$R_{DS(ON)} < 7m\Omega \quad (V_{GS} = -10V)$$

$$R_{DS(ON)} < 8m\Omega \quad (V_{GS} = -4.5V)$$

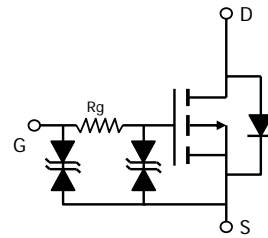
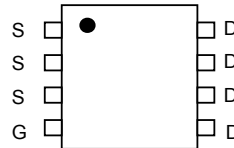


Fits SOIC8 footprint!



DFN5X6

Top View



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^G	I_D	$T_C=25^\circ\text{C}$	-30
		$T_C=100^\circ\text{C}$	-23
Pulsed Drain Current ^C	I_{DM}	-160	A
Continuous Drain Current	I_{DSM}	$T_A=25^\circ\text{C}$	-15
		$T_A=70^\circ\text{C}$	-12
Avalanche Current ^C	I_{AR}	-54	A
Repetitive avalanche energy $L=0.1\text{mH}$ ^C	E_{AR}	146	mJ
Power Dissipation ^B	P_D	$T_C=25^\circ\text{C}$	83
		$T_C=100^\circ\text{C}$	33
Power Dissipation ^A	P_{DSM}	$T_A=25^\circ\text{C}$	2.5
		$T_A=70^\circ\text{C}$	1.6
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	14.2	17	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{AD}		Steady-State	42	50
Maximum Junction-to-Case	$R_{\theta JC}$	1.2	1.5	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±16V			±10	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =-250μA	-0.8	-1.2	-1.6	V
I _{D(ON)}	On state drain current	V _{GS} =-10V, V _{DS} =-5V	-160			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-20A T _J =125°C		5.5 7	7 8.5	mΩ
		V _{GS} =-4.5V, I _D =-20A		6.1	8	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-20A		70		S
V _{SD}	Diode Forward Voltage	I _S =-1A, V _{GS} =0V		-0.65	-1	V
I _S	Maximum Body-Diode Continuous Current				-50	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, f=1MHz		4580	5500	pF
C _{oss}	Output Capacitance		755		pF	
C _{rss}	Reverse Transfer Capacitance		564		pF	
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		160	210	Ω
SWITCHING PARAMETERS						
Q _{g(-10V)}	Total Gate Charge	V _{GS} =-10V, V _{DS} =-15V, I _D =-20A		87	105	nC
Q _{g(-4.5V)}	Total Gate Charge		41		nC	
Q _{gs}	Gate Source Charge		12.8		nC	
Q _{gd}	Gate Drain Charge		17		nC	
t _{D(on)}	Turn-On Delay Time	V _{GS} =-10V, V _{DS} =-15V, R _L =0.75Ω, R _{GEN} =3Ω		180		ns
t _r	Turn-On Rise Time		260		ns	
t _{D(off)}	Turn-Off Delay Time		1.2		μs	
t _f	Turn-Off Fall Time		9.7		μs	
t _{rr}	Body Diode Reverse Recovery Time	I _F =-20A, di/dt=300A/μs		32	40	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-20A, di/dt=300A/μs		77		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The Power dissipation P_{DSM} is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

B: The power dissipation P_D is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J=25°C.

D: The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E: The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F: These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150°C. The SOA curve provides a single pulse rating.

G: The maximum current rating is limited by bond-wires.

H: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

Rev 0: July 2008

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

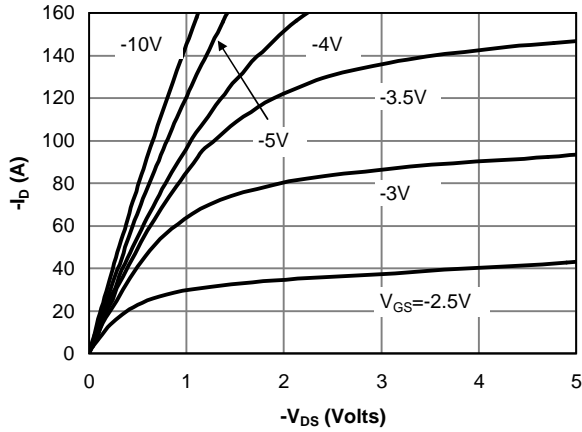


Figure 1: On-Region Characteristics (Note E)

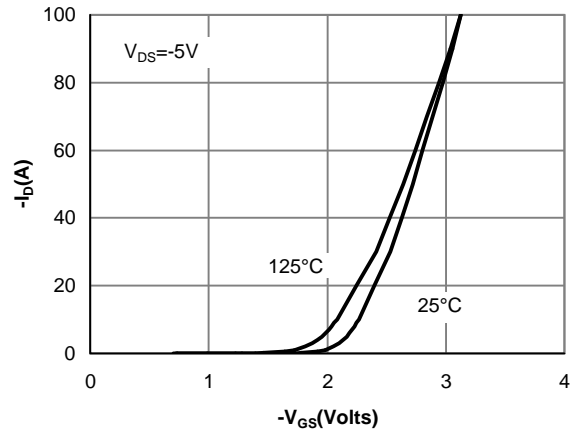


Figure 2: Transfer Characteristics (Note E)

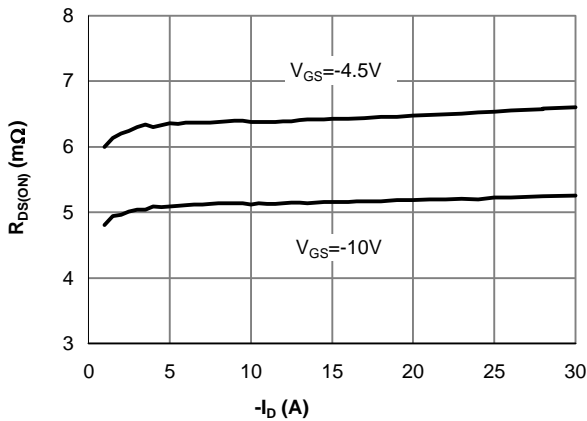


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

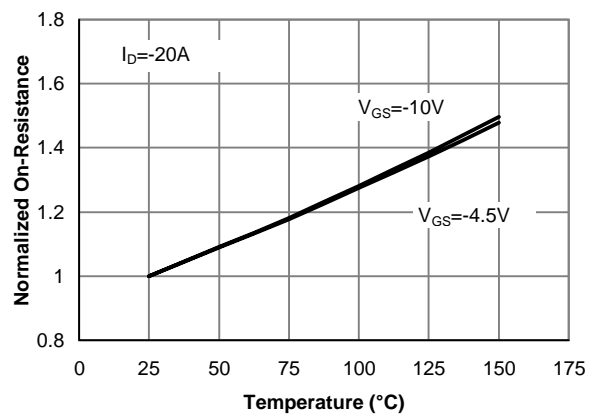


Figure 4: On-Resistance vs. Junction Temperature (Note E)

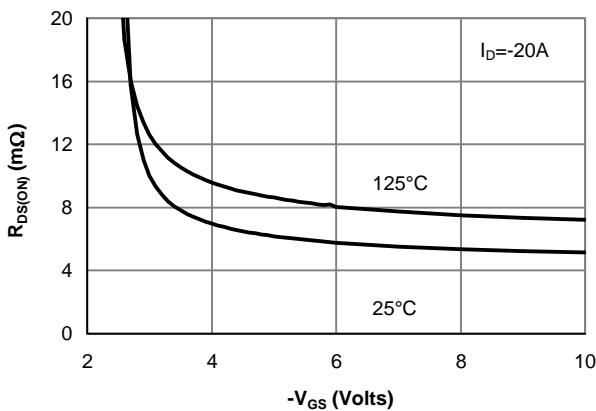


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

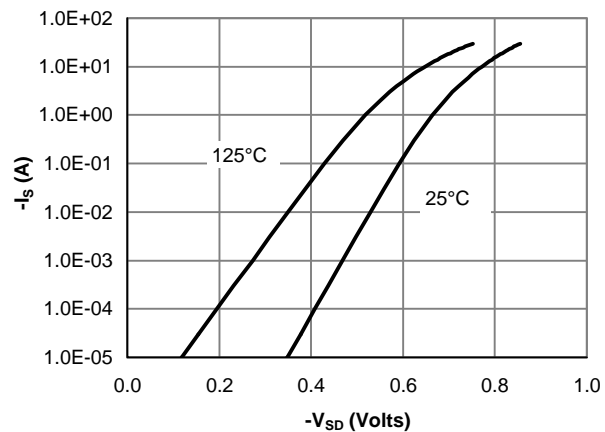


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

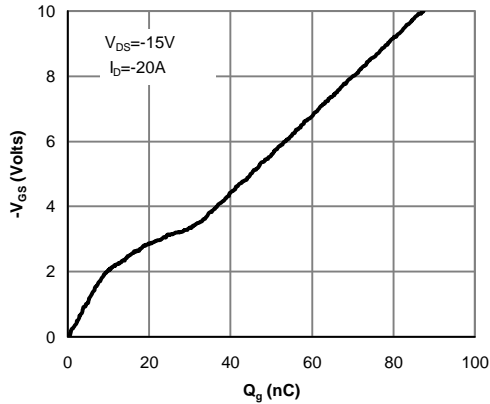


Figure 7: Gate-Charge Characteristics

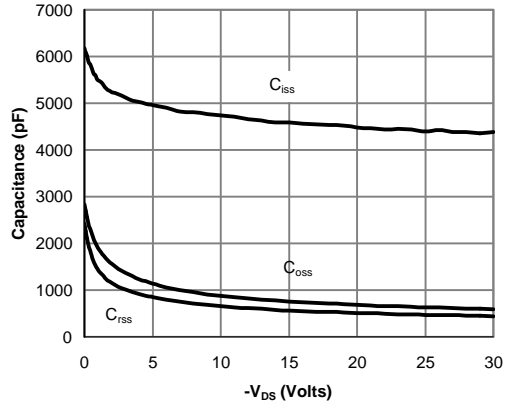


Figure 8: Capacitance Characteristics

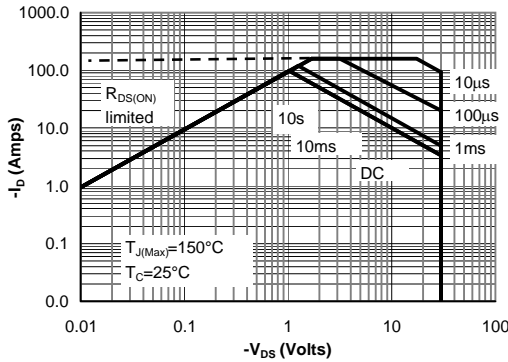


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

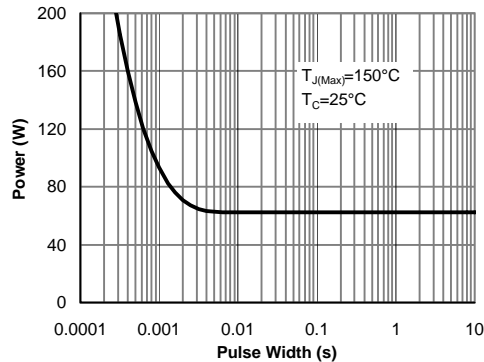


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

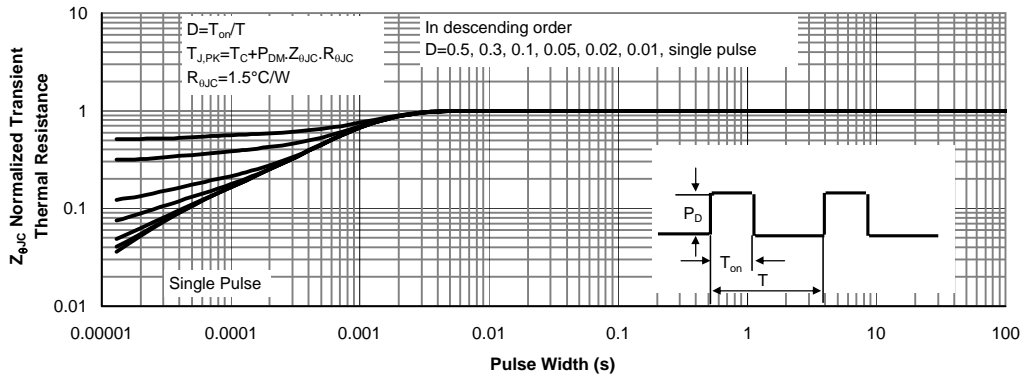
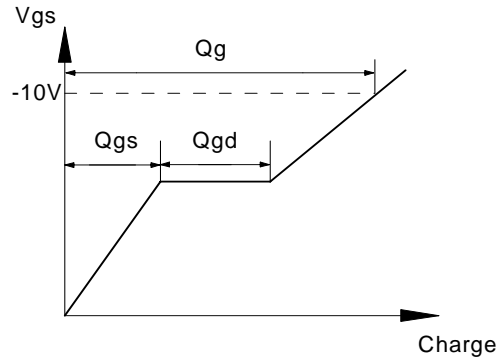
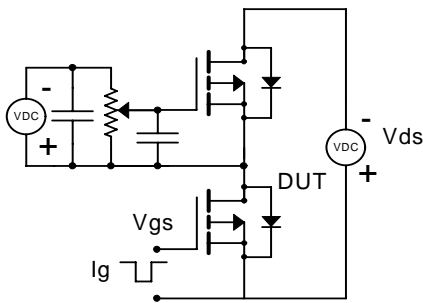
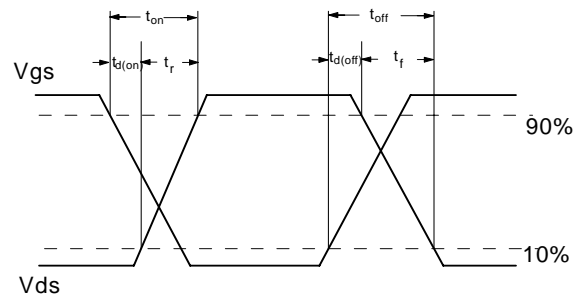
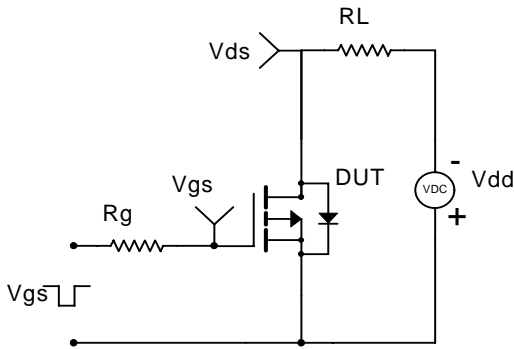


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

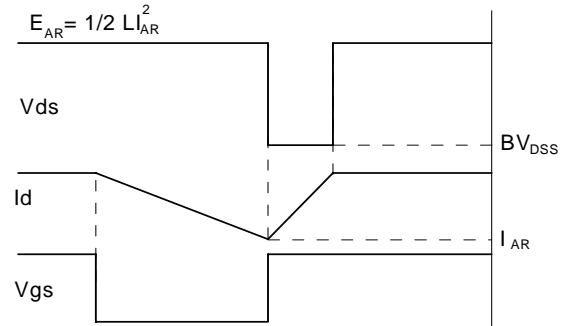
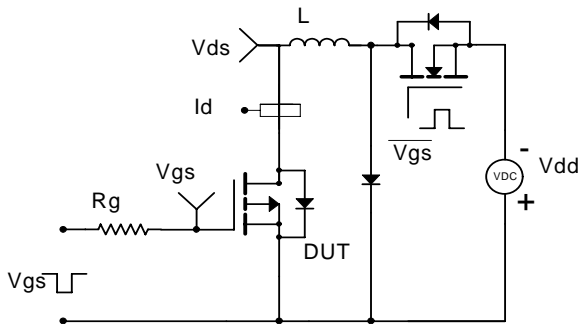
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

